

*SPECIFICATION AMENDMENTS*

Replace the paragraph beginning at page 1, line 16 with:

In recent years, the development of LSI technology has been significant, and the size of LSIs is becoming even-smaller. Thus, the width of wiring through which signals are transmitted is also getting smaller, i.e., wirings are becoming ultrathin. As the resistance values of conventional Tungsten (W) ~~film films~~ and Aluminium (Al) ~~film films~~ are ~~said to be~~ unable to withstand this thinning of the wire, the adoption of copper (Cu), which has a low resistance value, has been suggested.

Replace the paragraph beginning at page 5, line 7 with:

~~FIG. 1~~ The figure shows a schematic view for illustrating a film-forming apparatus (MOCVD).

Replace the paragraph beginning at page 12, line 4 with:

~~Fig. 1~~ The figure is a schematic view for illustrating a film-forming apparatus (MOCVD). In ~~Fig. 1~~, the figure the film-forming apparatus includes source material containers 1a and 1b, a heater 3, a decomposition reactor 4, a substrate 5, gas flow controllers 7, and a gas blowout shower head 9.

In re Appln. of MIKAMI et al.  
Application No. Unassigned

*AMENDMENTS TO THE DRAWINGS*

The attached sheet includes changes to the only figure to conform to U.S. practice.

Attachment: Replacement Sheet(s)